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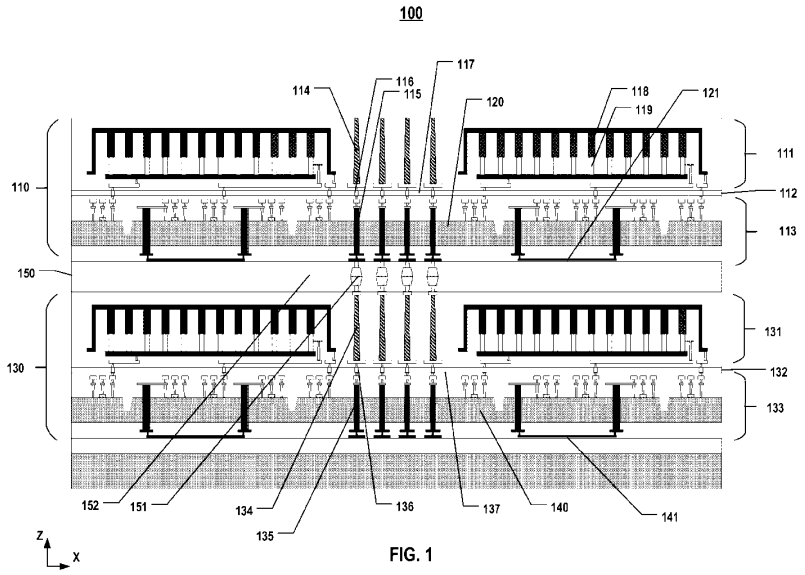

FIG. 1

(57) Abstract: A semiconductor structure includes a first semiconductor chip and a second semiconductor chip stacking with the first semiconductor chip along a first direction. The first semiconductor chip includes a first memory structure including a first contact structure extending along a first direction, and a first periphery structure disposed on a first substrate, the first periphery structure in contact with the first memory structure and including a second contact structure extending along the first direction. The second semiconductor chip is bonded to the first semiconductor chip through a chip-to-chip bonding layer, and the first contact structure and the second contact structure are coupled through a first coupling layer.

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